

1-Supplier	
Name	НІТАСНІ
2-Equipement Type	
Description	S-4700
3-Process	
Process type	FE-SEM
4-Wafer Type	
Wafer specification	-
5-Layout configuration	
Specific Layout defintion	Standard
6-CE Compliance	
7-Mainframe configuration	
Platform	
configuration	
Position 1	Body
Secondary electron resolution	1.5nm guarantee (acceleration voltage 15kV, WD = 12mm)
	2.5nm guaranteed (acceleration voltage 1KV, WD = 2.5mm)
magnification	LM mode x 20 ~ x 2k
	HM mode x 100- x 500k
Electro-optical system	
Electron gun	Cold cathode field emission electron gun
Acceleration voltage	0.5-30kV (0.1kV step)
Lens system	3-stage electromagnetic lens reduction method
Objective lens diaphragm	Movable aperture (4 holes can be switched and finely adjusted from m outside the vacu
Astigmatism correction coil	8-pole electromagnetic system (X, Y)
Scanning coil	Two-stage electromagnetic deflection method
Sample fine movement device	Туре II
Stage control	5-axis motor drive
Range of movement	
X	0-100mm
Y	0 to 50 mm
Z (WD)	2.5 to 30.0 mm
T (tilt angle)	-5-60 °
R (angle of rotation)	360 °
Sample exchange size	150mmφ (maximum)
Detector	: Secondary electron detector (Upper / Lower)
	(With noise removal function by beam monitor signal)
	Ultra-sensitive reflected electron detector
	Energy dispersive X-ray detector
Scan mode	Normal scan, selected area scan, line scan, photo scan,

	Spot position, average concentration distribution, dual mug / split, o
PC	Pentium 166MHz or higher
	Memory 32MB or more
	HD 2.4GB or more
	Microsoft Windows NT
monitor	For observation: 17-inch color CRT (1024x767 pixels)
Signal processing	Real-time image display
	Automatic image adjustment (brightness, contrast)
	Gamma control
	Derivative image display (contour enhancement)
	Inverted image display
	Autofocus (AFC)
	Auto stigma
	Memory photo (maximum 2560 x 1920 pixels)
	S / N improvement by averaging
	Image integration (maximum number of integrations 1024)
	Contrast conversion (memory image)
	Color display (two-color overlapping display and pseudo color)
	Beam blanking (when the image freezes)
	Raster rotation / tilt competition
Scanning speed	TV, slow 0.5-40s / frame: for observation
Electrical field of view movement	± 15 μm (when WD = 12 mm)
Frame memory capacity	TV, slow 0.5-40s / frame: for observation
······	± 15 μm (when WD = 12 mm)
	640 x 480 pixel image: 11 screens
Image display size	1280 x 960 pixel image: 11 screens
	2560 x 1920 pixel image: 2 sides
	Standard (640 x 480 pixels x 1)
Operating condition memory	2 screen display (512 x 480 pixels x 2)
Signal selection	Full surface (1024 x 700 pixels)
External control	Can be registered
	SE (secondary electron) signal, X-ray signal, AUX signal (2 systems
Main special accessories	DBC (Digital Beam Control)
Detector related	
Pre-processing related	YAG type reflected electron detector
	Energy Dispersive X-ray Analyzer (EX-200)
	E-1030 Mild sputtering equipment
display	(With evaporation unit)
	Multi-prep system
	DBC (Digital Beam Control)
	Ethernet network interface
	(LAN compatible, but does not include connection work)

	Video amplifier unit	
	Photomal power supply unit	
9-Chemical Solution configuration		
10- Workstation hardware configuration		
11-System software/ automation configuration		
12-Electrical		
13-Ancillaries		
14- Hook-up connexion / Specific requirement		
15-Options		
17- Target process performances		

Broken parts : Detector used for EDS (EOL detector) (EDS specification) Aztec Live Standard Ultim40 Detector:Ultim40(Resolution127eV@MnKα, 40mm2 polymer window) Soft package Standard + Option(TruMap/ AutoLock(drift correction)) Analyzer x4 PC(Windows10), 27 inch monitor Offline license Microsoft Office